METHOD FOR OPTIMIZING NILS OF EX-POSED LINES

Abstract

A method for optimizing NILS of exposed lines includes providing a photomask layout which has a first straight line and a second straight line parallel with the first straight line and is applied to a Quasar 90 illumination, and adding a first assist pattern between the first and second straight lines, wherein the first assist pattern has a plurality of geometric patterns with similar size arranging as a line parallel with the first straight line.